



BCW68H

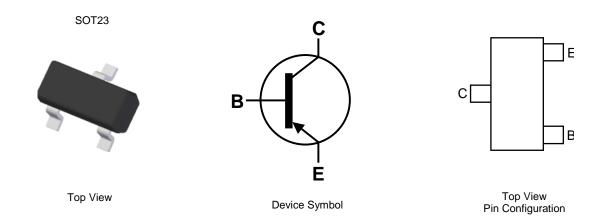
45V PNP MEDIUM POWER TRANSISTOR IN SOT23

#### **Features**

- BVCEO > -45V
- Ic = -800mA High Continuous Collector Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -300mV @ 100mA</li>
- Complementary NPN Type: BCW66H
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Mechanical Data**

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Paakaga	Morking	Reel Size (inches)	Tape Width (mm)	Packing		
Fart Number	Package	Marking Reel Size (inches)		Tape width (mm)	Qty.	Carrier	
BCW68HTA	SOT23	DH	7	8	3000	Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information

Notes:





# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CES</sub>	-60	V
Collector-Emitter Voltage	VCEO	-45	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	lc	-800	mA
Peak Pulse Current	Ісм	-1000	mA
Base Current	IB	-100	mA

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Discinction	(Note 5)	D_	310	mW	
Power Dissipation	(Note 6)	PD	350	TIVV	
Thermal Desistance Junction to Ambient	(Note 5)	0	403	0000	
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	°C/W	
Thermal Resistance, Junction to Leads	(Note 7)	Rejl	350	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes: 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; the device is measured when operating in a steady-state condition.

6. Same as Note 5, except the device is mounted on 15mm  $\times$  15mm FR4 PCB.

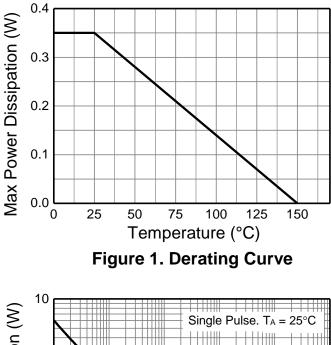
7. Thermal resistance from junction to solder-point (at the end of the leads).

8. Refer to JEDEC specification JS-001-2017, JS-002-2022 and JESD22-A115C.



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## **Thermal Characteristics**



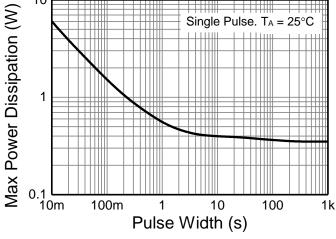


Figure 3. Pulse Power Dissipation

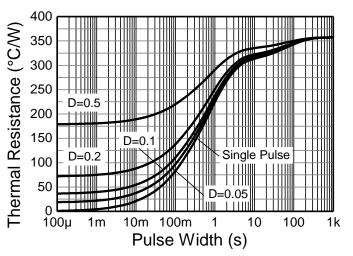


Figure 2. Transient Thermal Impedance



## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

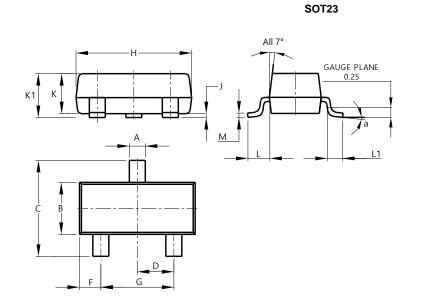
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS					•	
Collector-Base Breakdown Voltage	BVCES	-60	—	_	V	Ic = -10μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 9)	BV <sub>CEO</sub>	-45	_	—	V	I <sub>CEO</sub> = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7	—	_	V	I <sub>EBO</sub> = -10μA
Collector-Emitter Cut-Off Current	ICES		< 1 —	-20 -10	nA µA	V <sub>CES</sub> = -45V V <sub>CES</sub> = -45V, T <sub>A</sub> = +150°C
Emitter-Base Cut-Off Current	IEBO	_	< 1	-20	nA	VEBO = -5.6V
ON CHARACTERISTICS (Note 9)		•				•
Static Forward Current Transfer Ratio	hfe	180 250 100	 350 	630 —	_	IC = -10mA, V <sub>CE</sub> = -1V IC = -100mA, V <sub>CE</sub> = -1V IC = -500mA, V <sub>CE</sub> = -2V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_		-300	mV	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	-2	V	Ic = -500mA, I <sub>B</sub> = -50mA
SMALL SIGNAL CHARACTERISTICS (Note 9)	• • • •					-
Transition Frequency	f⊤	100	—	—	MHz	Ic = -20mA, Vce = -10V, f = 100MHz
Output Capacitance	Cobo	_	12	18	pF	V <sub>CB</sub> = -10V, f = 1MHz
Input Capacitance	Cibo	—	—	80	pF	V <sub>CB</sub> = -0.5V, f = 1MHz
Noise Figure	Ν	_	2	10	dB	$\label{eq:constraint} \begin{array}{l} I_C = -0.2 m A, \ V_{CE} = -5 V, \\ R_G = 1 k \Omega, \ f = 1 k H z, \\ \Delta f = 200 H z \end{array}$
Turn-On Time	t <sub>on</sub>	—	_	100	ns	$I_{C} = -150 \text{mA},$
Turn-Off Time	toff	_	_	400	ns	I <sub>B1</sub> = -I <sub>B2</sub> = -15mA, R <sub>L</sub> = 150Ω

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



### **Package Outline Dimensions**

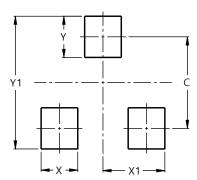
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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